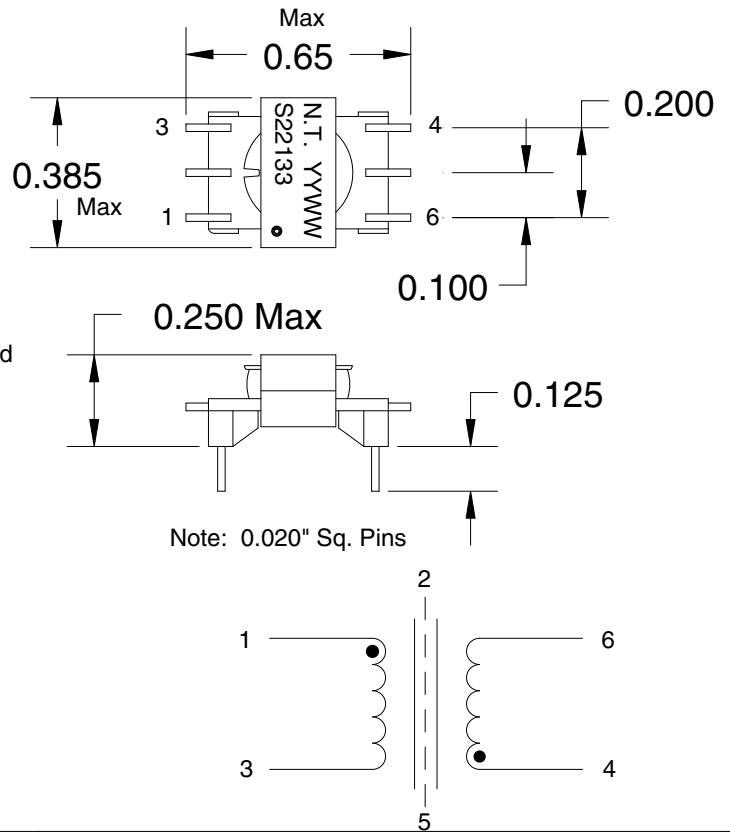


SPECIFICATIONS:

1. INDUCTANCE: @ 10 kHz, 0.1 Vrms,
1 - 3 > 225 uHy
2. DCR: mOHMS Nom
1 - 3 = 0.1
4 - 6 = 0.1
3. LEAKAGE INDUCTANCE: 1 - 3, 0.10 V @ 100kHz
SHORT 4 - 6 < 0.7 uHy
4. INTERWINDING CAPACITANCE: with Shield Grounded
1 - 3 to 4 - 6 @ 100 KHz, 1.0V < 2.0 pf
5. TURNS AND PHASE:
1 - 3 : 4 - 6 = 1 : 1 +/- 2%
- 6 DIELECTRIC STRENGTH:
1500 VAC 1 sec

Note: Designed to operate with Crystal Semiconductor
CS8401.8402, 8411 & 8412



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